

08-21-06

IFW



Appn. Number: 10/609.157

Appn. Filed: Jun/27/2003

Applicant: Hai Jiang

**Title: Programmable Metallization Cell Memory with
Multiple Extra-Small Resistive Elements**

Examiner: Pho M. Luu/2824

Aug. 17, 2006

Pleasanton, CA

Commissioner for Patents

P.O. Box 1450

Alexandria, Virginia 22313-1450

Sir,

Below is the response to the Office Action mailed on May. 19, 2006:

Claim rejections-35USC 102

*Claim 32-34 are rejected under 35 U.S.C. 102(e) as being anticipated by
Gliton. (US.2003/0194865).*

*Regarding claims 32-34, Gliton in Figure 3 disclosed a memory device
(memory cell 120) comprising:*

*A resistive layer with a plurality of solid electrolyte element (110) and a
metallic layer(112) and wherein the resistive layer is a layer with plurality of solid
electrolyte element(110)embedded in an insulator layer(200) and wherein the*